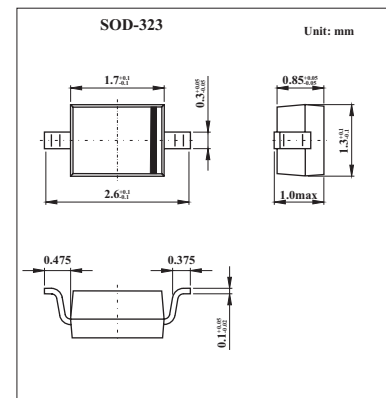


Silicon Epitaxial Planar Diode

1SV216

■ Features

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Peak Reverse Voltage	V_{RM}	35 ($R_L = 10K \Omega$)	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1 \mu\text{A}$	30			V
Reverse Current	I_R	$V_R = 28 \text{V}$			10	nA
Capacitance	C_{2V}	$f = 1 \text{MHz}; V_R = 2 \text{V}$	10.5		16	pF
	C_{10V}	$f = 1 \text{MHz}; V_R = 10 \text{V}$	3.3		5.7	
Capacitance Ratio	C_{2V}/C_{10V}		2.5		3.4	
Series Resistance	r_s	$V_R = 5 \text{V}, f = 470 \text{MHz}$		0.55	1.2	Ω

■ Marking

Marking	T4
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